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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	e200z4
Core Size	32-Bit Single-Core
Speed	150MHz
Connectivity	CANbus, EBI/EMI, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	84
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.14V ~ 5.25V
Data Converters	A/D 40x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=spc5642af2mlu1

Qorivva MPC5642A Microcontroller Data Sheet

- 150 MHz e200z4 Power Architecture core
 - Variable length instruction encoding (VLE)
 - Superscalar architecture with 2 execution units
 - Up to 2 integer or floating point instructions per cycle
 - Up to 4 multiply and accumulate operations per cycle
- Memory organization
 - 2 MB on-chip flash memory with ECC and read-while-write (RWW)
 - 128 KB on-chip SRAM with standby functionality (32 KB) and ECC
 - 8 KB instruction cache (with line locking), configurable as 2- or 4-way
 - 14 + 3 KB eTPU code and data RAM
 - 4 × 4 crossbar switch (XBAR)
 - 24-entry MMU
- Fail Safe Protection
 - 16-entry Memory Protection Unit (MPU)
 - CRC unit with 3 submodules
 - Junction temperature sensor
- Interrupt
 - Configurable interrupt controller (INTC) with non-maskable interrupt (NMI)
 - 64-channel eDMA
- Serial channels
 - 3 eSCI modules
 - 3 DSPI modules (2 of which support downstream Micro Second Channel [MSC])
 - 3 FlexCAN modules with 64 message buffers each
 - 1 FlexRay module (V2.1) up to 10 Mbit/s w/dual or single channel, 128 message objects, ECC
- 1 eMIOS
 - 24 unified channels
- 1 eTPU2 (second generation eTPU)
 - 32 standard channels

MPC5642A



- 1 reaction module (6 channels with 3 outputs per channel)
- 2 enhanced queued analog-to-digital converters (eQADCs)
 - Forty 12-bit input channels (multiplexed on 2 ADCs); expandable to 56 channels with external multiplexers
 - 6 command queues
 - Trigger and DMA support
 - 688 ns minimum conversion time
- On-chip CAN/SCI Bootstrap loader with Boot Assist Module (BAM)
- Nexus: Class 3+ for core; Class 1 for eTPU
- JTAG (5-pin)
- Development Trigger Semaphore (DTS)
 - EVTO pin for communication with external tool
- Clock generation
 - On-chip 4–40 MHz main oscillator
 - On-chip FMPLL (frequency-modulated phase-locked loop)
- Up to 112 general purpose I/O lines
 - Individually programmable as input, output or special function
 - Programmable threshold (hysteresis)
- Power reduction modes: slow, stop, and standby
- Flexible supply scheme
 - 5 V single supply with external ballast
 - Multiple external supply: 5 V, 3.3 V, and 1.2 V

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- An access protection error is detected if a memory reference does not hit in any memory region or the reference is flagged as illegal in all memory regions where it does hit. In the event of an access error, the XBAR reference is terminated with an error response and the MPU inhibits the bus cycle being sent to the targeted slave device
- 64-bit error registers, one for each XBAR slave port, capture the last faulting address, attributes, and detail information

1.5.6 Frequency-modulated phase-locked loop (FMPLL)

The FMPLL allows the user to generate high speed system clocks from a 4 MHz to 40 MHz crystal oscillator or external clock generator. Further, the FMPLL supports programmable frequency modulation of the system clock. The PLL multiplication factor, output clock divider ratio are all software configurable. The PLL has the following major features:

- Input clock frequency from 4 MHz to 40 MHz
- Reduced frequency divider (RFD) for reduced frequency operation without forcing the PLL to relock
- 3 modes of operation
 - Bypass mode with PLL off
 - Bypass mode with PLL running (default mode out of reset)
 - PLL normal mode
- Each of the 3 modes may be run with a crystal oscillator or an external clock reference
- Programmable frequency modulation
 - Modulation enabled/disabled through software
 - Triangle wave modulation up to 100 kHz modulation frequency
 - Programmable modulation depth (0% to 2% modulation depth)
 - Programmable modulation frequency dependent on reference frequency
- Lock detect circuitry reports when the PLL has achieved frequency lock and continuously monitors lock status to report loss of lock conditions
- Clock Quality Module
 - Detects the quality of the crystal clock and causes interrupt request or system reset if error is detected
 - Detects the quality of the PLL output clock; if error detected, causes system reset or switches system clock to crystal clock and causes interrupt request
- Programmable interrupt request or system reset on loss of lock
- Self-coded mode (SCM) operation

1.5.7 System integration unit (SIU)

The MPC5642A SIU controls MCU reset configuration, pad configuration, external interrupt, general purpose I/O (GPIO), internal peripheral multiplexing, and the system reset operation. The reset configuration block contains the external pin boot configuration logic. The pad configuration block controls the static electrical characteristics of I/O pins. The GPIO block provides uniform and discrete input/output control of the I/O pins of the MCU. The reset controller performs reset monitoring of internal and external reset sources, and drives the RSTOUT pin. Communication between the SIU and the e200z4 CPU core is via the crossbar switch. The SIU provides the following features:

- System configuration
 - MCU reset configuration via external pins
 - Pad configuration control for each pad
 - Pad configuration control for virtual I/O via DSPI serialization
- System reset monitoring and generation
 - Power-on reset support
 - Reset status register provides last reset source to software

- 3 channels' internal timebases sharable between channels
- 1 timebase from eTPU2 can be imported and used by the channels
- Global enable feature for all eMIOS and eTPU timebases
- Dedicated pin for each channel (not available on all package types)
- Each channel (0–23) supports the following functions:
 - General Purpose Input/Output (GPIO)
 - Single Action Input Capture (SAIC)
 - Single Action Output Compare (SAOC)
 - Output Pulse Width Modulation Buffered (OPWMB)
 - Input Period Measurement (IPM)
 - Input Pulse Width Measurement (IPWM)
 - Double Action Output Compare (DOAC)
 - Modulus Counter Buffered (MCB)
 - Output Pulse Width & Frequency Modulation Buffered (OPWFMB)
- Each channel has its own pin (not available on all package types)

1.5.12 Second generation enhanced time processing unit (eTPU2)

The eTPU2 is an enhanced co-processor designed for timing control. Operating in parallel with the host CPU, the eTPU2 processes instructions and real-time input events, performs output waveform generation, and accesses shared data without host intervention. Consequently, for each timer event, the host CPU setup and service times are minimized or eliminated. A powerful timer subsystem is formed by combining the eTPU2 with its own instruction and data RAM. High-level assembler/compiler and documentation allows customers to develop their own functions on the eTPU2.

MPC5642A devices feature the second generation of the eTPU, called eTPU2. Enhancements of the eTPU2 over the standard eTPU include:

- The Timer Counter (TCR1), channel logic and digital filters (both channel and the external timer clock input [TCRCLK]) now have an option to run at full system clock speed or system clock / 2.
- Channels support unordered transitions: transition 2 can now be detected before transition 1. Related to this enhancement, the transition detection latches (TDL1 and TDL2) can now be independently negated by microcode.
- A new User Programmable Channel Mode has been added: the blocking, enabling, service request and capture characteristics of this channel mode can be programmed via microcode.
- Microinstructions now provide an option to issue Interrupt and Data Transfer requests selected by channel. They can also be requested simultaneously at the same instruction.
- Channel Flags 0 and 1 can now be tested for branching, in addition to selecting the entry point.
- Channel digital filters can be bypassed.

The eTPU2 includes these distinctive features:

- 32 channels; each channel associated with one input and one output signal
 - Enhanced input digital filters on the input pins for improved noise immunity
 - Identical, orthogonal channels: each channel can perform any time function. Each time function can be assigned to more than one channel at a given time, so each signal can have any functionality.
 - Each channel has an event mechanism which supports single and double action functionality in various combinations. It includes two 24-bit capture registers, two 24-bit match registers, 24-bit greater-equal and equal-only comparators.
 - Input and output signal states visible from the host
- 2 independent 24-bit time bases for channel synchronization:
 - First time base clocked by system clock with programmable prescale division from 2 to 512 (in steps of 2), or by output of second time base prescaler

- Second time base counter can work as a continuous angle counter, enabling angle based applications to match angle instead of time
- Both time bases can be exported to the eMIOS timer module
- Both time bases visible from the host
- Event-triggered microengine:
 - Fixed-length instruction execution in two-system-clock microcycle
 - 14 KB of code memory (SCM)
 - 3 KB of parameter (data) RAM (SPRAM)
 - Parallel execution of data memory, ALU, channel control and flow control sub-instructions in selected combinations
 - 32-bit microengine registers and 24-bit wide ALU, with 1 microcycle addition and subtraction, absolute value, bitwise logical operations on 24-bit, 16-bit, or byte operands, single-bit manipulation, shift operations, sign extension and conditional execution
 - Additional 24-bit Multiply/MAC/Divide unit which supports all signed/unsigned Multiply/MAC combinations, and unsigned 24-bit divide. The MAC/Divide unit works in parallel with the regular microcode commands.
- Resource sharing features support channel use of common channel registers, memory and microengine time:
 - Hardware scheduler works as a “task management” unit, dispatching event service routines by predefined, host-configured priority
 - Automatic channel context switch when a “task switch” occurs, that is, one function thread ends and another begins to service a request from other channel: channel-specific registers, flags and parameter base address are automatically loaded for the next serviced channel
 - SPRAM shared between host CPU and eTPU2, supporting communication either between channels and host or inter-channel
 - Hardware implementation of 4 semaphores support coherent parameter sharing between both eTPU engines
 - Dual-parameter coherency hardware support allows atomic access to 2 parameters by host
- Test and development support features:
 - Nexus Class 1 debug, supporting single-step execution, arbitrary microinstruction execution, hardware breakpoints and watchpoints on several conditions
 - Software breakpoints
 - SCM continuous signature-check built-in self test MISC (multiple input signature calculator), runs concurrently with eTPU2 normal operation

1.5.13 Reaction module (REACM)

The REACM provides the ability to modulate output signals to manage closed loop control without CPU assistance. It works in conjunction with the eQADC and eTPU2 to increase system performance by removing the CPU from the current control loop.

The REACM has the following features:

- 6 reaction channels with peak and hold control blocks
- Each channel output is a bus of 3 signals, providing ability to control 3 inputs.
- Each channel can implement a peak and hold waveform, making it possible to implement up to six independent peak and hold control channels

Target applications include solenoid control for direct injection systems and valve control in automatic transmissions.

1.5.16 Enhanced serial communications interface (eSCI)

Three eSCI modules provide asynchronous serial communications with peripheral devices and other MCUs, and include support to interface to Local Interconnect Network (LIN) slave devices. Each eSCI block provides the following features:

- Full-duplex operation
- Standard mark/space non-return-to-zero (NRZ) format
- 13-bit baud rate selection
- Programmable 8-bit or 9-bit data format
- Programmable 12-bit or 13-bit data format for Timed Serial Bus (TSB) configuration to support the Microsecond bus standard
- Automatic parity generation
- LIN support
 - Compatible with LIN slaves from revisions 1.x and 2.0 of the LIN standard
 - Autonomous transmission of entire frames
 - Configurable to support all revisions of the LIN standard
 - Automatic parity bit generation
 - Double stop bit after bit error
 - 10- or 13-bit break support
- Separately enabled transmitter and receiver
- Programmable transmitter output parity
- 2 receiver wake-up methods:
 - Idle line wake-up
 - Address mark wake-up
- Interrupt-driven operation with flags
- Receiver framing error detection
- Hardware parity checking
- 1/16 bit-time noise detection
- DMA support for both transmit and receive data
 - Global error bit stored with receive data in system RAM to allow post processing of errors

1.5.17 Controller area network (FlexCAN)

The MPC5642A MCU includes three FlexCAN blocks. The FlexCAN module is a communication controller implementing the CAN protocol according to Bosch Specification version 2.0B. The CAN protocol was designed to be used primarily as a vehicle serial data bus, meeting the specific requirements of this field: real-time processing, reliable operation in the EMI environment of a vehicle, cost-effectiveness and required bandwidth. Each FlexCAN module contains 64 message buffers.

The FlexCAN modules provide the following features:

- Based on and including all existing features of the Freescale TouCAN module
- Full Implementation of the CAN protocol specification, Version 2.0B
 - Standard data and remote frames
 - Extended data and remote frames
 - Zero to eight bytes data length
 - Programmable bit rate up to 1 Mbit/s
- Content-related addressing
- 64 message buffers of 0 to 8 bytes data length
- Individual Rx Mask Register per message buffer

Table 3. MPC5642A signal properties (continued)

Name ¹	Function ²	P / A / G ³	PCR PA field ⁴	PCR ⁵	I/O type	Voltage ⁶ / Pad type ⁷	Status ⁸		Package pin No.		
							During reset	After reset	176	208	324
AN37	Single-ended Analog Input	P	—	—	I	VDDA / Analog	I / —	AN[37] / —	175	E3	A5
AN38	Single-ended Analog Input	P	—	—	I	VDDA / Analog	I / —	AN[38] / —	—	—	D3
AN39	Single-ended Analog Input	P	—	—	I	VDDA / Analog	I / —	AN[39] / —	8	D2	D2
VRH	Voltage Reference High	P	—	—	I	VDDA / —	I / —	—	163	A8	A10
VRL	Voltage Reference Low	P	—	—	I	VDDA / —	I / —	—	162	A9	A11
REFBYBC	Reference Bypass Capacitor Input	P	—	—	I	VDDA / Analog	I / —	—	164	B7	B10
eTPU2											
TCRCLKA IRQ[7] GPIO[113]	eTPU A TCR clock External interrupt request GPIO	P A1 G	01 10 00	113	I — I/O	VDDEH4 / Slow	— / Up	— / Up	—	L4	AB12
ETPUA0 ETPUA12_O ETPUA19_O GPIO[114]	eTPU A channel eTPU A channel (output only) eTPU A channel (output only) GPIO	P A1 A2 G	001 010 100 000	114	I/O O O I/O	VDDEH4 / Slow	— / WKPCFG	— / WKPCFG	61	N3	Y12
ETPUA1 ETPUA13_O GPIO[115]	eTPU A channel eTPU A channel (output only) GPIO	P A1 G	01 10 00	115	I/O O I/O	VDDEH4 / Slow	— / WKPCFG	— / WKPCFG	60	M3	W12
ETPUA2 ETPUA14_O GPIO[116]	eTPU A channel eTPU A channel (output only) GPIO	P A1 G	01 10 00	116	I/O O I/O	VDDEH4 / Slow	— / WKPCFG	— / WKPCFG	59	P2	AA11
ETPUA3 ETPUA15_O GPIO[117]	eTPU A channel eTPU A channel (output only) GPIO	P A1 G	01 10 00	117	I/O O I/O	VDDEH4 / Slow	— / WKPCFG	GPIO / WKPCFG	58	P1	Y11
ETPUA4 ETPUA16_O — FR_B_TX GPIO[118]	eTPU A channel eTPU A channel (output only) — FlexRay transmit data channel B GPIO	P A1 A2 A3 G	0001 0010 — 1000 0000	118	I/O O — O I/O	VDDEH4 / Slow	— / WKPCFG	— / WKPCFG	56	N2	W11
ETPUA5 ETPUA17_O DSPI_B_SCK_LVDS— FR_B_TX_EN GPIO[119]	eTPU A channel eTPU A channel (output only) LVDS negative DSPI clock FlexRay tx data enable for ch. B GPIO	P A1 A2 A3 G	0001 0010 0100 1000 0000	119	I/O O O O I/O	VDDEH4 / Slow + LVDS	— / WKPCFG	— / WKPCFG	54	M4	AB11

Table 3. MPC5642A signal properties (continued)

Name ¹	Function ²	P / A / G ³	PCR PA field ⁴	PCR ⁵	I/O type	Voltage ⁶ / Pad type ⁷	Status ⁸		Package pin No.		
							During reset	After reset	176	208	324
EMIOS6 ETPUA6_O GPIO[185]	eMIOS channel eTPU A channel (output only) GPIO	P A1 G	01 10 00	185	I/O O I/O	VDDEH4 / Slow	— / Down	— / Down	68	P7	AA14
EMIOS7 ETPUA7_O GPIO[186]	eMIOS channel eTPU A channel (output only) GPIO	P A1 G	01 10 00	186	I/O O I/O	VDDEH4 / Slow	— / Down	— / Down	69	—	AB14
EMIOS8 ETPUA8_O SCI_B_TX GPIO[187]	eMIOS channel eTPU A channel (output only) eSCI B transmit GPIO	P A1 A2 G	001 010 100 000	187	I/O O O I/O	VDDEH4 / Slow	— / Up	— / Up	70	P8	W15
EMIOS9 ETPUA9_O SCI_B_RX GPIO[188]	eMIOS channel eTPU A channel (output only) eSCI B receive GPIO	P A1 A2 G	001 010 100 000	188	I/O O — I/O	VDDEH4 / Slow	— / Up	— / Up	71	R7	Y15
EMIOS10 DSPI_D_PCS[3] RCH3_B GPIO[189]	eMIOS channel DSPI D peripheral chip select Reaction channel 3B GPIO	P A1 A2 G	001 010 100 000	189	I/O O O I/O	VDDEH4 / Medium	— / WKPCFG	— / WKPCFG	73	N8	AA15
EMIOS11 DSPI_D_PCS[4] RCH3_C GPIO[190]	eMIOS channel DSPI D peripheral chip select Reaction channel 3C GPIO	P A1 A2 G	001 010 100 000	190	I/O O O I/O	VDDEH4 / Medium	— / WKPCFG	— / WKPCFG	75	R8	AB15
EMIOS12 DSPI_C_SOUT ETPUA27_O GPIO[191]	eMIOS channel DSPI C data output eTPU A channel (output only) GPIO	P A1 A2 G	001 010 100 000	191	I/O O O I/O	VDDEH4 / Medium	— / WKPCFG	— / WKPCFG	76	N10	AB16
EMIOS13 DSPI_D_SOUT GPIO[192]	eMIOS channel DSPI D data output GPIO	P A1 G	01 10 00	192	I/O O I/O	VDDEH4 / Medium	— / WKPCFG	— / WKPCFG	77	T8	AA16
EMIOS14 IRQ[0] ETPUA29_O GPIO[193]	eMIOS channel External interrupt request eTPU A channel (output only) GPIO	P A1 A2 G	001 010 100 000	193	I/O — O I/O	VDDEH4 / Slow	— / Down	— / Down	78	R9	Y16
EMIOS15 IRQ[1] GPIO[194]	eMIOS channel External interrupt request GPIO	P A1 G	01 10 00	194	I/O — I/O	VDDEH4 / Slow	— / Down	— / Down	79	T9	W16
EMIOS16 GPIO[195]	eMIOS channel GPIO	P G	01 00	195	I/O I/O	VDDEH4 / Slow	— / Up	— / Up	—	—	W17
EMIOS17 GPIO[196]	eMIOS channel GPIO	P G	01 00	196	I/O I/O	VDDEH4 / Slow	— / Up	— / Up	—	—	Y17
EMIOS18 GPIO[197]	eMIOS channel GPIO	P G	01 00	197	I/O I/O	VDDEH4 / Slow	— / Up	— / Up	—	—	AA17
EMIOS19 GPIO[198]	eMIOS channel GPIO	P G	01 00	198	I/O I/O	VDDEH4 / Slow	— / WKPCFG	— / WKPCFG	—	—	AB17

3.3 Thermal characteristics

Table 9. Thermal characteristics for 176-pin LQFP¹

Symbol	C	Parameter	Conditions	Value	Unit
R _{θJA}	CC	Junction-to-ambient, natural convection ²	Single-layer board – 1s	38	°C/W
R _{θJA}	CC	Junction-to-ambient, natural convection ²	Four-layer board – 2s2p	31	°C/W
R _{θJMA}	CC	Junction-to-moving-air, ambient ²	at 200 ft./min., single-layer board – 1s	30	°C/W
	CC		at 200 ft./min., four-layer board – 2s2p	25	°C/W
R _{θJB}	CC	Junction-to-board ³		20	°C/W
R _{θJCtop}	CC	Junction-to-case ⁴		5	°C/W
Ψ _{JT}	CC	Junction-to-package top, natural convection ⁵		2	°C/W

¹ Thermal characteristics are targets based on simulation that are subject to change per device characterization.

² Junction-to-Ambient Thermal Resistance determined per JEDEC JESD51-3 and JESD51-6. Thermal test board meets JEDEC specification for this package.

³ Junction-to-Board thermal resistance determined per JEDEC JESD51-8. Thermal test board meets JEDEC specification for the specified package.

⁴ Junction-to-Case at the top of the package determined using MIL-STD 883 Method 1012.1. The cold plate temperature is used for the case temperature. Reported value includes the thermal resistance of the interface layer.

⁵ Thermal characterization parameter indicating the temperature difference between the package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

Table 10. Thermal characteristics for 208-pin MAPBGA¹

Symbol	C	Parameter	Conditions	Value	Unit
R _{θJA}	CC	Junction-to-ambient, natural convection ²	Single layer board – 1s ³	39	°C/W
	CC		Four layer board – 2s2p ⁴	24	°C/W
R _{θJMA}	CC	Junction-to-moving-air, ambient ²	at 200 ft./min., single-layer board – 1s ⁴	31	°C/W
	CC		at 200 ft./min., four-layer board – 2s2p	20	°C/W
R _{θJB}	CC	Junction-to-board ⁵	Four-layer board – 2s2p	13	°C/W
R _{θJC}	CC	Junction-to-case ⁶		6	°C/W
Ψ _{JT}	CC	Junction-to-package top natural convection ⁷		2	°C/W

¹ Thermal characteristics are targets based on simulation that are subject to change per device characterization.

² Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.

³ Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal

⁴ Per JEDEC JESD51-6 with the board horizontal

⁵ Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.

⁶ Indicates the average thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1) with the cold plate temperature used for the case temperature.

3.5 Electrostatic discharge (ESD) characteristics

Table 13. ESD ratings^{1,2}

Symbol	Parameter		Conditions	Value	Unit
—	SR	ESD for Human Body Model (HBM)	—	2000	V
R1	SR	HBM circuit description	—	1500	Ω
C	SR		—	100	pF
—	SR	ESD for Field Induced Charge Model (FDCM)	All pins	500	V
—			Corner pins	750	
—	SR	Number of pulses per pin	Positive pulses (HBM)	1	—
—			Negative pulses (HBM)	1	—
—	SR	Number of pulses	—	1	—

¹ All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.

² Device failure is defined as: "If after exposure to ESD pulses, the device does not meet the device specification requirements, which includes the complete DC parametric and functional testing at room temperature and hot temperature."

3.6 Power management control (PMC) and power on reset (POR) electrical specifications

Table 14. PMC operating conditions and external regulators supply voltage

ID	Name	C	Parameter	Value			Unit
				Min	Typ	Max	
1	T _J	SR	Junction temperature	-40	27	150	°C
2	V _{DDREG}	SR	PMC 5 V supply voltage VDDREG	4.75	5	5.25	V
3	V _{DD}	CC	Core supply voltage 1.2 V VDD when external regulator is used without disabling the internal regulator (PMC unit turned on, LVI monitor active) ¹	1.26 ²	1.3	1.32	V
3a	—	CC	Core supply voltage 1.2 V VDD when external regulator is used with a disabled internal regulator (PMC unit turned-off, LVI monitor disabled)	1.14	1.2	1.32	V
4	I _{VDD}	CC	Voltage regulator core supply maximum required DC output current	400	—	—	mA
5	V _{DD33}	CC	Regulated 3.3 V supply voltage when external regulator is used without disabling the internal regulator (PMC unit turned-on, internal 3.3V regulator enabled, LVI monitor active) ³	3.3	3.45	3.6	V
5a	—	CC	Regulated 3.3 V supply voltage when external regulator is used with a disabled internal regulator (PMC unit turned-off, LVI monitor disabled)	3	3.3	3.6	V
6	—	CC	Voltage regulator 3.3 V supply maximum required DC output current	80	—	—	mA

¹ An internal regulator controller can be used to regulate the core supply.

² The minimum supply required for the part to exit reset and enter in normal run mode is 1.28 V.

³ An internal regulator can be used to regulate the 3.3 V supply.

Table 20. DC electrical specifications¹ (continued)

Symbol	C	Parameter	Conditions	Value			Unit	
				Min	Typ	Max		
V _{IL_LS}	SR	P	Multi-voltage I/O pad input low voltage in Low-swing-mode ^{7,8,9,10}	Hysteresis enabled	V _{SS} – 0.3	—	0.8	V
		P		Hysteresis disabled	V _{SS} – 0.3	—	0.9	
V _{IL_HS}	SR	P	Multi-voltage pad I/O input low voltage in high-swing-mode	Hysteresis enabled	V _{SS} – 0.3	—	0.35 V _{DDEH}	V
		P		Hysteresis disabled	V _{SS} – 0.3	—	0.4 V _{DDEH}	
V _{IH_S}	SR	P	Slow/medium pad I/O input high voltage	Hysteresis enabled	0.65 V _{DDEH}	—	V _{DDEH} + 0.3	V
		P		Hysteresis disabled	0.55 V _{DDEH}	—	V _{DDEH} + 0.3	
V _{IH_F}	SR	P	Fast I/O input high voltage	Hysteresis enabled	0.65 V _{DDE}	—	V _{DDE} + 0.3	V
		P		Hysteresis disabled	0.58 V _{DDE}	—	V _{DDE} + 0.3	
V _{IH_LS}	SR	P	Multi-voltage pad I/O input high voltage in low-swing-mode ^{7,8,9,10}	Hysteresis enabled	2.5	—	V _{DDE} + 0.3	V
		P		Hysteresis disabled	2.2	—	V _{DDE} + 0.3	
V _{IH_HS}	SR	P	Multi-voltage I/O input high voltage in high-swing-mode	Hysteresis enabled	0.65 V _{DDEH}	—	V _{DDEH} + 0.3	V
		P		Hysteresis disabled	0.55 V _{DDEH}	—	V _{DDEH} + 0.3	
V _{OL_S}	CC	P	Slow/medium pad I/O output low voltage ¹¹	—	—	—	0.2 * V _{DDEH}	V
V _{OL_F}	CC	P	Fast I/O output low voltage ¹¹	—	—	—	0.2 * V _{DDE}	V
V _{OL_LS}	CC	P	Multi-voltage pad I/O output low voltage in low-swing mode ^{7,8,9,10,11}	—	—	—	0.6	V
V _{OL_HS}	CC	P	Multi-voltage pad I/O output low voltage in high-swing mode ¹¹	—	—	—	0.2 V _{DDEH}	V
V _{OH_S}	CC	P	Slow/medium I/O output high voltage ¹¹	—	0.8 V _{DDEH}	—	—	V
V _{OH_F}	CC	P	Fast pad I/O output high voltage ¹¹	—	0.8 V _{DDE}	—	—	V
V _{OH_LS}	CC	P	Multi-voltage pad I/O output high voltage in low-swing mode ^{7,8,9,10,11}	—	2.3	3.1	3.7	V
V _{OH_HS}	CC	P	Multi-voltage pad I/O output high voltage in high-swing mode ¹¹	—	0.8 V _{DDEH}	—	—	V
V _{HYS_S}	CC	P	Slow/medium/multi-voltage I/O input hysteresis	—	0.1 * V _{DDEH}	—	—	V
V _{HYS_F}	CC	P	Fast I/O input hysteresis	—	0.1 * V _{DDE}	—	—	V
V _{HYS_LS}	CC	C	Low-swing-mode multi-voltage I/O input hysteresis	Hysteresis enabled	0.25	—	—	v

Table 24. DSPI LVDS pad specification (continued)

Symbol	C	Parameter	Condition	Value			Unit
				Min	Typ	Max	
T _{SKEW}	CC	D	Differential skew t _{phla-tphlbl} or t _{phlb-tphlal}	—	—	—	0.5 ns
Termination							
	CC	D	Transmission line (differential Zo)	—	95	100	105 W
	CC	D	Temperature	—	-40	—	150 °C

3.10 Oscillator and PLLMRFM electrical characteristics

Table 25. PLLMRFM electrical specifications¹(V_{DDPLL} = 1.08 V to 3.6 V, V_{SS} = V_{SSPLL} = 0 V, T_A = T_L to T_H)

Symbol	C	Parameter	Conditions	Value		Unit	
				Min	Max		
f _{ref_crystal} f _{ref_ext}	CC	P	PLL reference frequency range ²	Crystal reference	4	40	MHz
				External reference	4	80	
f _{pll_in}	CC	D	Phase detector input frequency range (after pre-divider)	—	4	16	MHz
f _{vco}	CC	D	VCO frequency range	—	256	512	MHz
f _{sys}	CC	T	On-chip PLL frequency ²	—	16	150	MHz
f _{sys}	CC	T	System frequency in bypass mode ³	Crystal reference	4	40	MHz
				External reference	0	80	
t _{CYC}	CC	D	System clock period	—	—	1 / f _{sys}	ns
f _{LORL} f _{LORH}	CC	D	Loss of reference frequency window ⁴	Lower limit	1.6	3.7	MHz
				Upper limit	24	56	
f _{SCM}	CC	P	Self-coded mode frequency ^{5,6}	—	1.2	72.25	MHz
C _{JITTER}	CC	C	CLKOUT period jitter ^{7,8,9,10}	f _{SYS} maximum	-5	5	% f _{CLKOUT}
					-6	6	
t _{cst}	CC	T	Crystal start-up time ^{11,12}	—	—	10 ms	
V _{IHEXT}	CC	D	EXTAL input high voltage	Crystal mode ¹³	V _{xtal} + 0.4	—	V
				External reference ^{13,14}	V _{RC33} /2 + 0.4	V _{RC33}	

Table 29. eQADC differential ended conversion specifications (operating) (continued)

Symbol	C	Parameter	Value		Unit		
			min	max			
DIFF _{max}	CC	C	Maximum differential voltage (DANx+ - DANx-) or (DANx- - DANx+) ⁵	PREGAIN set to 1X setting	—	(VRH - VRL)/2	V
DIFF _{max2}	CC	C		PREGAIN set to 2X setting	—	(VRH - VRL)/4	V
DIFF _{max4}	CC	C		PREGAIN set to 4X setting	—	(VRH - VRL)/8	V
DIFF _{cmv}	CC	C	Differential input Common mode voltage (DANx- + DANx+)/2 ⁵	—	(V _{RH} + V _{RL})/2 - 5%	(V _{RH} + V _{RL})/2 + 5%	V

¹ Applies only to differential channels.

² Variable gain is controlled by setting the PRE_GAIN bits in the ADC_ACR1-8 registers to select a gain factor of $\times 1$, $\times 2$, or $\times 4$. Settings are for differential input only. Tested at $\times 1$ gain. Values for other settings are guaranteed by as indicated.

³ At $V_{RH} - V_{RL} = 5.12$ V, one LSB = 1.25 mV.

⁴ Guaranteed 10-bit mono tonicity.

⁵ Voltages between VRL and VRH will not cause damage to the pins. However, they may not be converted accurately if the differential voltage is above the maximum differential voltage. In addition, conversion errors may occur if the common mode voltage of the differential signal violates the Differential Input common mode voltage specification.

3.13 Configuring SRAM wait states

Use the SWSC field in the ECSM_MUDCR register to specify an additional wait state for the device SRAM. By default, no wait state is added.

Table 30. Cutoff frequency for additional SRAM wait state

1	SWSC Value
98	0
153	1

¹ Max frequencies including 2% PLL FM.

Please see the device reference manual for details.

3.14 Platform flash controller electrical characteristics

Table 31. APC, RWSC, WWSC settings vs. frequency of operation¹

Max. Flash Operating Frequency (MHz) ²	APC ³	RWSC ³	WWSC
20 MHz	0b000	0b000	0b01
61 MHz	0b001	0b001	0b01
90 MHz	0b010	0b010	0b01
123 MHz	0b011	0b011	0b01
153 MHz	0b100	0b100	0b01

¹ APC, RWSC and WWSC are fields in the flash memory BIUCR register used to specify wait states for address pipelining and read/write accesses. Illegal combinations exist—all entries must be taken from the same row.

² Max frequencies including 2% PLL FM.

³ APC must be equal to RWSC.

3.15 Flash memory electrical characteristics

Table 32. Flash program and erase specifications¹

#	Symbol	C	Parameter	Value				Unit
				Min	Typ	Initial max ²	Max ³	
1	T _{dwp}	CC	Double Word (64 bits) Program Time	—	30	—	500	μs
2	T _p	CC	Page Program Time ⁴	—	40	160	500	μs
3	T _{16k}	CC	16 KB Block Pre-program and Erase Time	—	250	1,000	5,000	ms
5	T _{64k}	CC	64 KB Block Pre-program and Erase Time	—	450	1,800	5,000	ms
6	T _{128k}	CC	128 KB Block Pre-program and Erase Time	—	800	2,600	7,500	ms
7	T _{256k}	CC	256 KB Block Pre-program and Erase Time	—	1,400	5,200	15,000	ms
8	T _{psrt}	SR	Program suspend request rate ⁵	100	—	—	—	μs
9	T _{esrt}	SR	Erase suspend request rate ⁶	10	—	—	—	ms

¹ Typical program and erase times assume nominal supply values and operation at 25 °C. All times are subject to change pending device characterization.

² Initial factory condition: ≤ 100 program/erase cycles, 25 °C, typical supply voltage, 80 MHz minimum system frequency.

³ The maximum erase time occurs after the specified number of program/erase cycles. This maximum value is characterized but not guaranteed.

⁴ Page size is 128 bits (4 words)

⁵ Time between program suspend resume and the next program suspend request.

⁶ Time between erase suspend resume and the next erase suspend request.

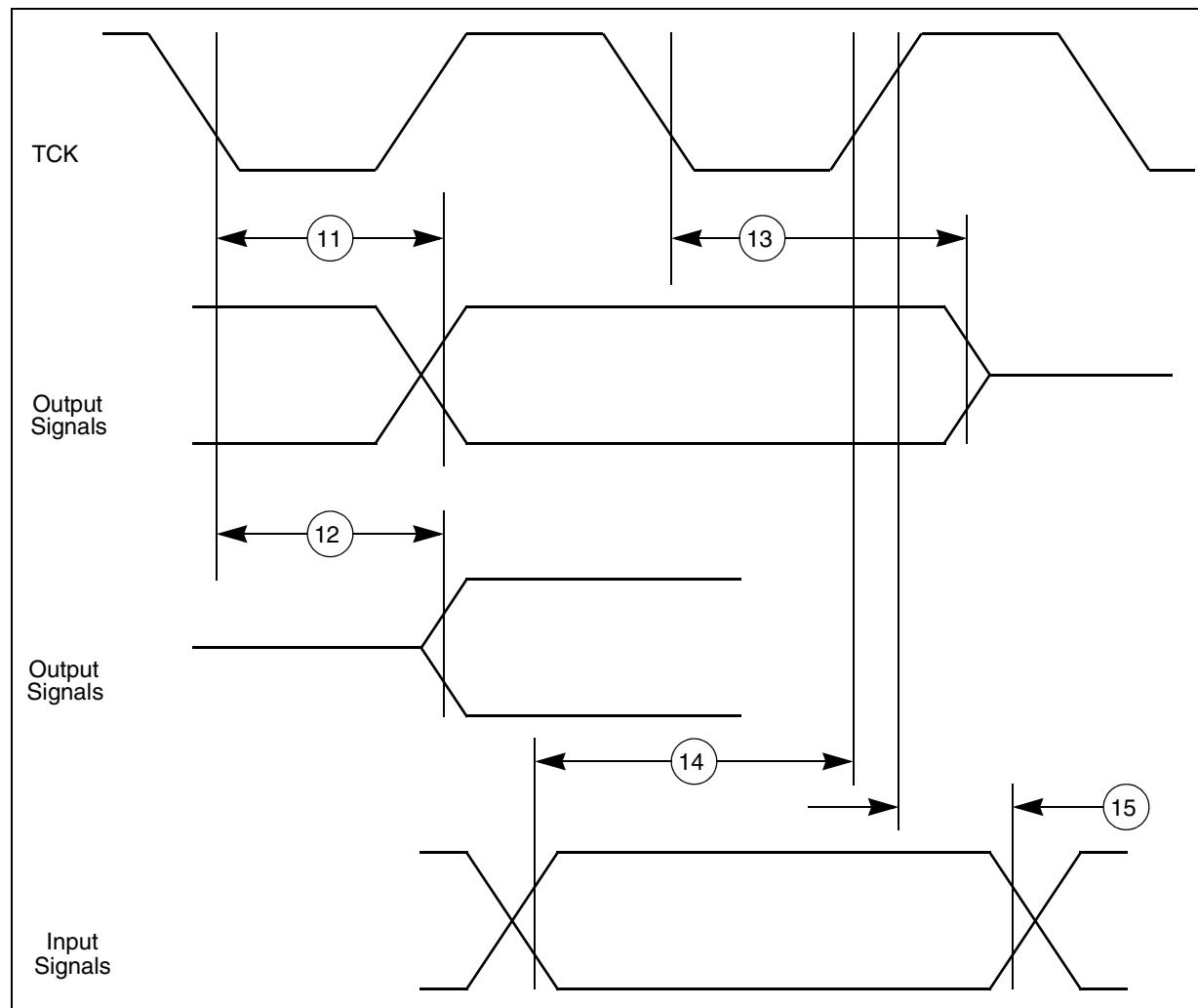


Figure 15. JTAG boundary scan timing

3.17.3 Nexus timing

Table 38. Nexus debug port timing¹

#	Symbol	C	Characteristic	Value		Unit
				Min	Max	
1	t_{MCYC}	CC D	MCKO Cycle Time	2 ^{2,3}	8	t_{CYC}
1a	t_{MCYC}	CC D	Absolute Minimum MCKO Cycle Time	25 ⁴	—	ns
2	t_{MDC}	CC D	MCKO Duty Cycle	40	60	%
3	t_{MDOV}	CC D	MCKO Low to MDO Data Valid ⁵	-0.1	0.35	t_{MCYC}
4	t_{MSEOV}	CC D	MCKO Low to \overline{MSEO} Data Valid ⁵	-0.1	0.35	t_{MCYC}
6	t_{EVTOV}	CC D	MCKO Low to \overline{EVTO} Data Valid ⁵	-0.1	0.35	t_{MCYC}
7	t_{EVTIPW}	CC D	\overline{EVTI} Pulse Width	4.0	—	t_{TCYC}

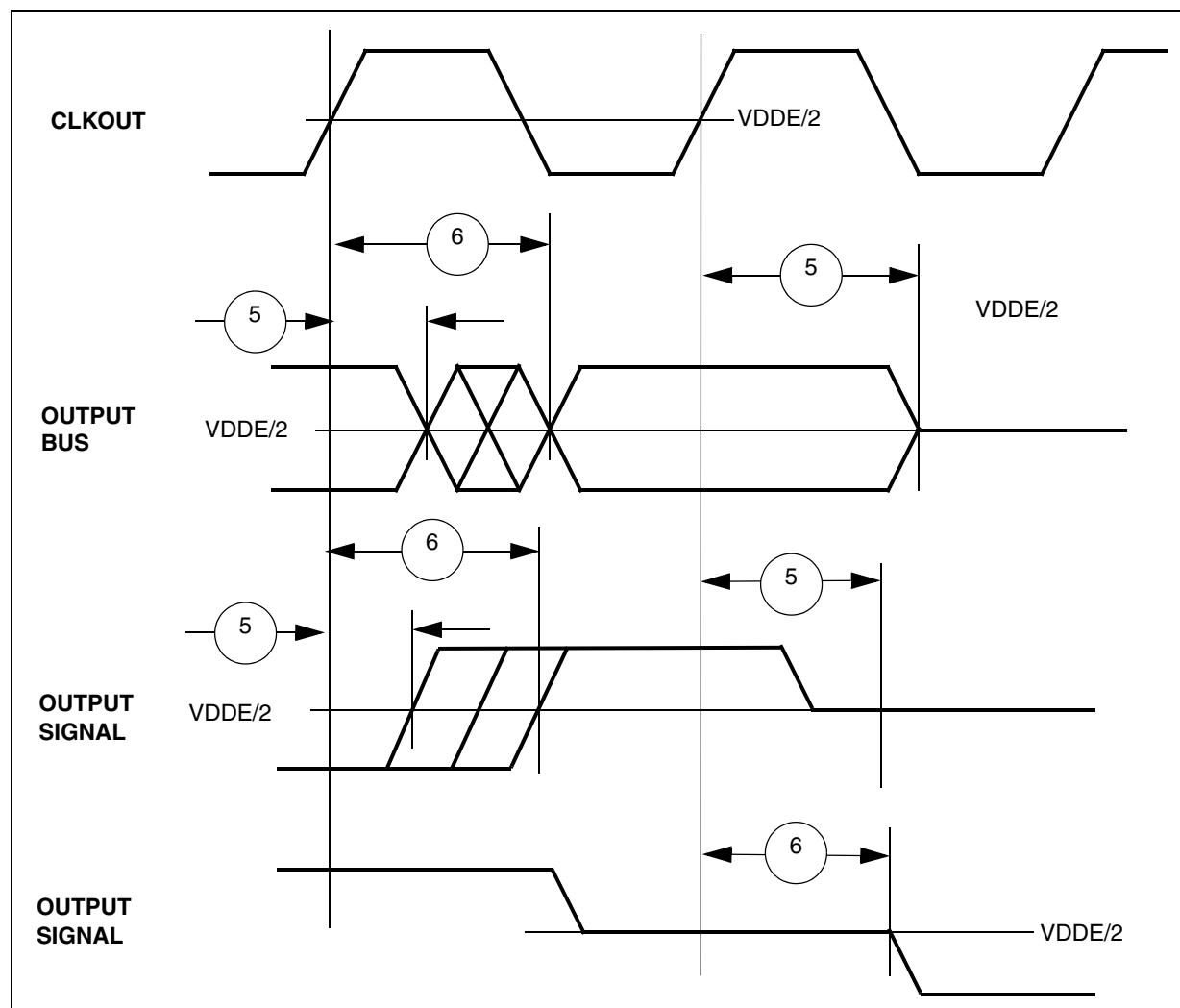


Figure 20. Synchronous output timing

3.17.10 FlexCAN system clock source

Table 48. FlexCAN engine system clock divider threshold

#	Symbol	Characteristic	Value	Unit
1	f_{CAN_TH}	FlexCAN engine system clock threshold	100	MHz

Table 49. FlexCAN engine system clock divider

System frequency	Required SIU_SYSDIV[CAN_SRC] value
$\leq f_{CAN_TH}$	0 ^{1,2}
$> f_{CAN_TH}$	1 ^{2,3}

¹ Divides system clock source for FlexCAN engine by 1

² System clock is only selected for FlexCAN when CAN_CR[CLK_SRC] = 1

³ Divides system clock source for FlexCAN engine by 2

NOTES:

1. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25MM PER SIDE. DIMENSIONS D1 AND E1 DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE DATUM H.
2. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE MAXIMUM b DIMENSION BY MORE THAN 0.08MM. DAMBAR CAN NOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM DISTANCE BETWEEN PROTRUSION AND AN ADJACENT LEAD IS 0.07MM FOR 0.4MM AND 0.5MM PITCH PACKAGES.

DIM	MIN	NOM	MAX	DIM	MIN	NOM	MAX	DIM	MIN	NOM	MAX
A	---	1.6		L1	1	REF					
A1	0.05	0.15		R1	0.08	---					
A2	1.35	1.4	1.45	R2	0.08	0.2					
b	0.17	0.22	0.27	S	0.2	REF					
b1	0.17	0.2	0.23	Ø	0°	3.5°	7°				
c	0.09	0.2		Ø1	0°	---					
c1	0.09	0.16		Ø2	11°	12°	13°				
D	26	BSC		Ø3	11°	12°	13°				
D1	24	BSC									
e	0.5	BSC									
E	26	BSC									
E1	24	BSC									
L	0.45	0.6	0.75		UNIT		DIMENSION AND TOLERANCES		REFERENCE DOCUMENT		
					MM		ASME Y14.5M		64-06-280-1392		
TITLE: LQFP 176LD 24X24X1.4 PKG 0.5 PITCH POD 2mm FOOTPRINT					COMPANY				ASECL		
					SHEET				3		

Figure 36. 176 LQFP package mechanical drawing (part 3)

4.1.3 324 TEPBGA

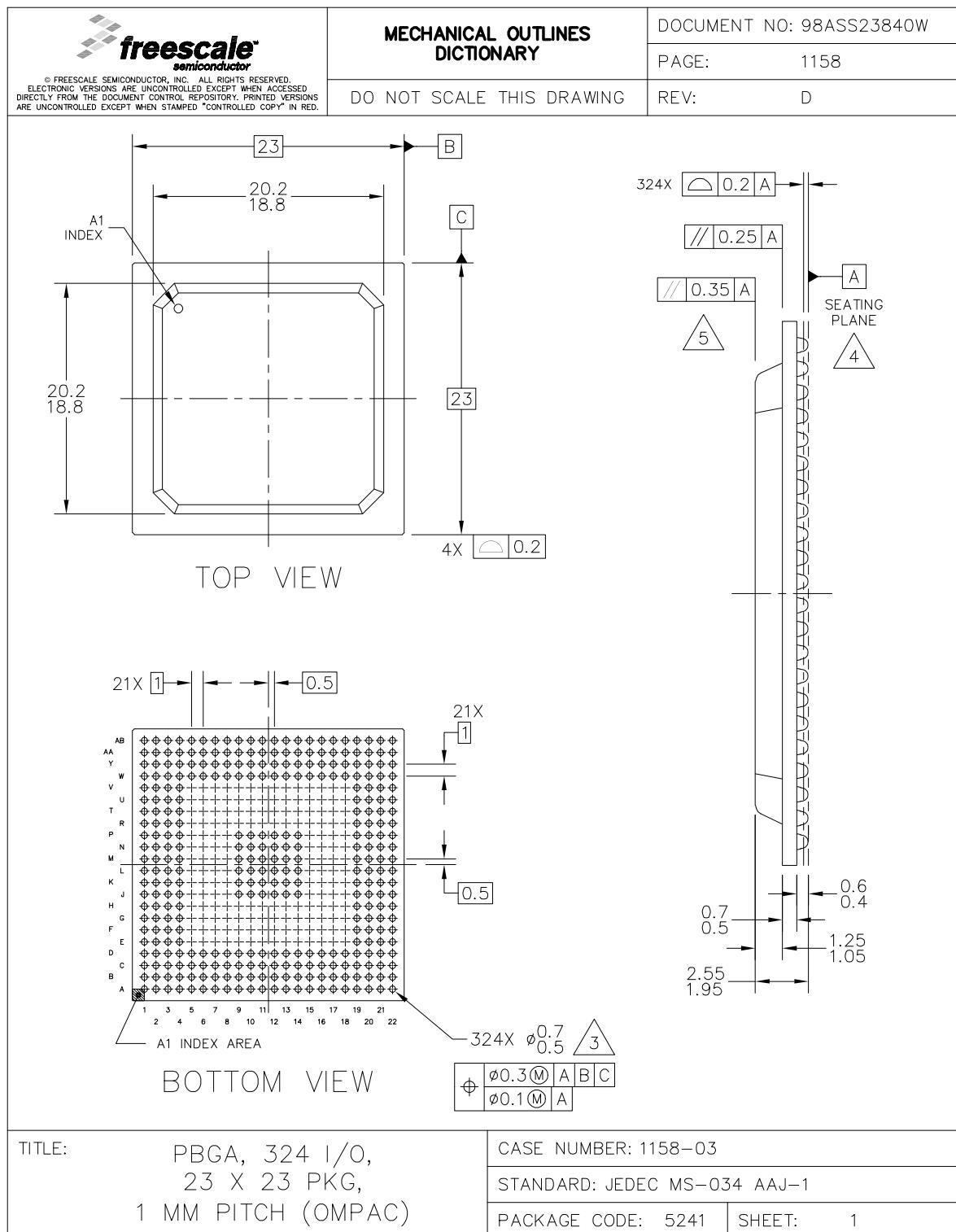


Figure 39. 324 BGA package mechanical drawing (part 1)

6 Document revision history

Table 51 summarizes customer facing revisions to this document.

Table 51. Revision history

Date	Revision	Substantive changes
05 Oct 2010	1	Initial release
26 Mar 2012	2	<p>Figure 1 (MPC5642A series block diagram), added ECSM block and its definition in the legend.</p> <p>Table 2 (MPC5642A series block summary), added the following blocks: REACN, SIU, ECSM, FMPLL, PIT and SWT.</p> <p>Updated Table 8 (Absolute maximum ratings)</p> <p>In 3, Electrical characteristics, deleted the “Recommended operating conditions” subsection.</p> <p>Table 14 (PMC operating conditions and external regulators supply voltage), removed minimum value of V_{DDREG} and its footnote.</p> <p>Updated Table 15 (PMC electrical characteristics)</p> <p>Updated Section 3.6.1, Regulator example</p> <p>Updated Table 20 (DC electrical specifications)</p> <p>Figure 8 (Core voltage regulator controller external components preferred configuration), added “T1” label to indicate the transistor.</p> <p>Table 20 (DC electrical specifications), changed maximum value of V_{IL_LS} to 0.9, was 1.1</p> <p>Table 21 (I/O pad average I_{DDE} specifications), in the V_{DDE} column changed all 5.5 to 5.25</p> <p>Table 24 (DSPI LVDS pad specification):</p> <ul style="list-style-type: none"> Renamed V_{OC}, was V_{OD} Updated minimum and maximum value of V_{OC} deleted all footnote <p>Table 26 (Temperature sensor electrical characteristics), updated minimum and maximum value of accuracy</p> <p>Updated Section 3.12, eQADC electrical characteristics</p> <p>Added Section 3.13, Configuring SRAM wait states</p> <p>Updated Table 31 (APC, RWSC, WWSC settings vs. frequency of operation)</p> <p>Updated Table 32 (Flash program and erase specifications)</p> <p>Table 31 (APC, RWSC, WWSC settings vs. frequency of operation), changed all values in the WWSC column to 0b01.</p> <p>Updated Table 32 (Flash program and erase specifications)</p> <p>Table 33 (Flash EEPROM module life):</p> <ul style="list-style-type: none"> updated temperature value in the Retention description (was 150 °C, is 85 °C) added values for Retention <p>Table 34 (Pad AC specifications ($V_{DDE} = 4.75$ V)):</p> <ul style="list-style-type: none"> changed maximum value of Medium to 12/12 changed maximum value of Slow to 20/20 <p>Updated Table 35 (Pad AC specifications ($V_{DDE} = 3.0$ V))</p> <p>Table 37 (JTAG pin AC electrical characteristics):</p> <ul style="list-style-type: none"> changed all parameter classification to D changed minimum value of t_{TMSS}, t_{TDIS} to 10 <p>Updated Table 38 (Nexus debug port timing)</p> <p>Added Table 39 (Nexus debug port operating frequency)</p> <p>Table 39 (Nexus debug port operating frequency), added a footnote near the value of t_{AAI}</p> <p>Table 44 (eMIOS timing):</p> <ul style="list-style-type: none"> changed minimum value of t_{MOPW} to 1 removed the footnote of t_{MOPW}